

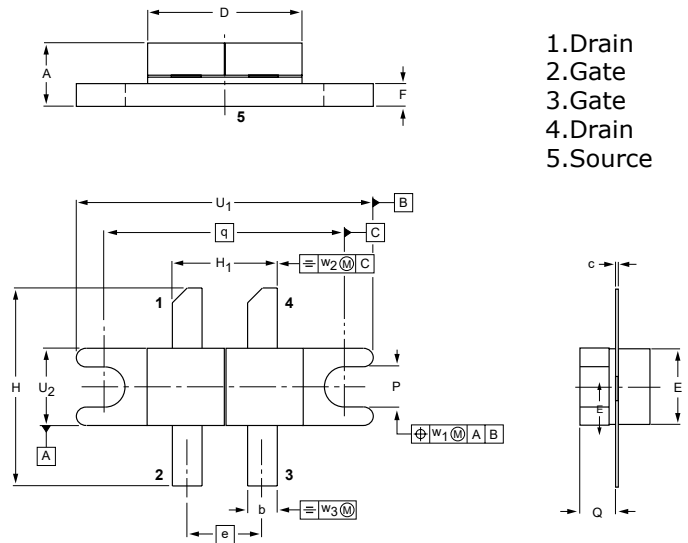
DESCRIPTION

Silicon N-channel enhancement mode vertical D-MOS transistor designed for HF/VHF/UHF applications

FEATURES

- Output Power: 40 W
- Power Gain: 13 dB Typ@400M, 28V
- Power Gain: 17 dB Typ@175M, 28V

DIMENSIONS



UNIT	A	b	c	D	E	e	F	H	H ₁	p	Q	q	U ₁	U ₂	w ₁	w ₂	w ₃
mm	4.91 4.19	1.66 1.39	0.13 0.07	12.96 12.44	6.48 6.22	6.45	2.04 1.77	17.02 16.00	8.23 7.72	3.43 3.17	2.67 2.41	18.42	24.90 24.63	6.61 6.35	0.51	1.02	0.26
inches	0.193 0.165	0.065 0.055	0.005 0.003	0.510 0.490	0.255 0.245	0.254	0.080 0.070	0.670 0.630	0.324 0.304	0.135 0.125	0.105 0.095	0.725	0.980 0.970	0.260 0.250	0.02	0.04	0.01

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Drain-Source Breakdown Voltage	V _{DS}	65	V
Drain-Source Breakdown Voltage (R _{GS} =1.0MΩ)	V _{DGR}	65	V
Gate-Source Voltage	V _{GS}	±40	V
Drain Current — Continuous	I _D	8	A
Total Device Dissipation	P _D	175	W
Junction Temperature	T _J	200	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	V _{(BR)DS}	I _D =5mA, V _{GS} =0	65	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =28V	-	-	1	mAdc
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±40V, V _{DS} =0V	-	-	1	uAdc
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =10V, I _D =25mA	1.0	-	6.0	V
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =1.5A	0.6	0.8	-	S
Input Capacitance	C _{iss}	V _{DS} =28V, V _{GS} =0V, f=1.0MHz	-	40	-	pF
Output Capacitance	C _{oss}		-	45	-	pF
Reverse Transfer Capacitance	C _{rss}		-	5	-	pF
Common Source Power Gain	G _p	V _{DD} =28V, P _{OUT} =40W, f=400MHz	11.0	13.0	-	dB
Drain Efficiency	η _D		45.0	50.0	-	%

Note : Above parameters , ratings , limits and conditions are subject to change.